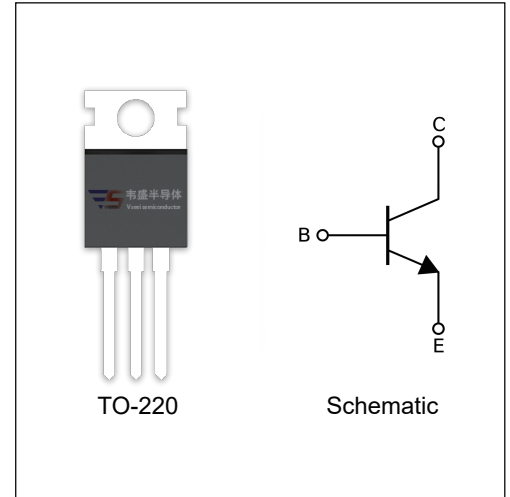


2SD882 TRANSISTOR (NPN)

FEATURES

- ☒ Power Dissipation



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	3	A
P _C	Collector Power Dissipation	2	W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V(\text{BR})_{\text{CBO}}$	$I_C = 100\mu\text{A}$, $I_E=0$	40			V
Collector-emitter breakdown voltage	$V(\text{BR})_{\text{CEO}}$	$I_C = 10\text{mA}$, $I_B=0$	30			V
Emitter-base breakdown voltage	$V(\text{BR})_{\text{EBO}}$	$I_E = 100\mu\text{A}$, $I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{\text{CB}} = 40\text{ V}$, $I_E=0$			1	μA
Collector cut-off current	I_{CEO}	$V_{\text{CE}} = 30\text{ V}$, $I_B=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{\text{EB}} = 6\text{ V}$, $I_C=0$			1	μA
DC current gain	h_{FE}	$V_{\text{CE}} = 2\text{ V}$, $I_C = 1\text{A}$	60		400	
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_C = 2\text{A}$, $I_B = 0.2\text{ A}$			0.5	V
Base-emitter saturation voltage	$V_{\text{BE(sat)}}$	$I_C = 2\text{A}$, $I_B = 0.2\text{ A}$			1.5	V
Transition frequency	f_{T}	$V_{\text{CE}} = 5\text{V}$, $I_C=0.1\text{A}$ $f = 10\text{MHz}$		90		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

Static Characteristic
